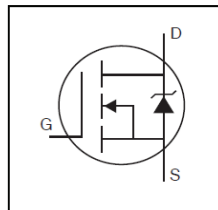
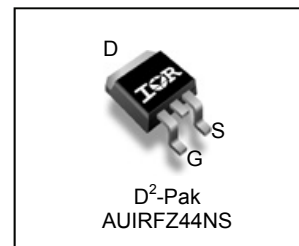


Features

- Advanced Planar Technology
- Low On-Resistance
- Dynamic dV/dT and dI/dT capability
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



V_{DSS}	55V
R_{DS(on)} max.	17.5mΩ
I_D	49A



G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRFZ44NS	D ² -Pak	Tube	50	AUIRFZ44NS
		Tape and Reel Left	800	AUIRFZ44NSTRL

Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	49	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	35	
I _{DM}	Pulsed Drain Current ①	160	
P _D @ T _A = 25°C	Maximum Power Dissipation	3.8	W
P _D @ T _C = 25°C	Maximum Power Dissipation	94	
	Linear Derating Factor	0.63	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS} (Thermally Limited)	Single Pulse Avalanche Energy (Thermally Limited) ⑥	150	mJ
E _{AS} (Tested)	Single Pulse Avalanche Energy (Tested Limited) ⑤	530	
I _{AR}	Avalanche Current ①	25	A
E _{AR}	Repetitive Avalanche Energy ①	9.4	mJ
dv/dt	Peak Diode Recovery ③	5.0	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.5	°C/W
R _{θJA}	Junction-to-Ambient (PCB Mount), D ² Pak	—	40	

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*Qualification standards can be found at www.infineon.com

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.058	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	17.5	mΩ	V _{GS} = 10V, I _D = 25A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Trans conductance	19	—	—	S	V _{DS} = 25V, I _D = 25A
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 55V, V _{GS} = 0V
		—	—	250		V _{DS} = 44V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

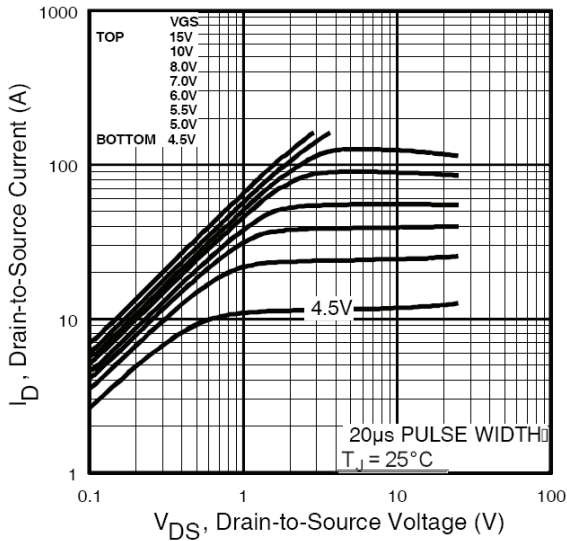
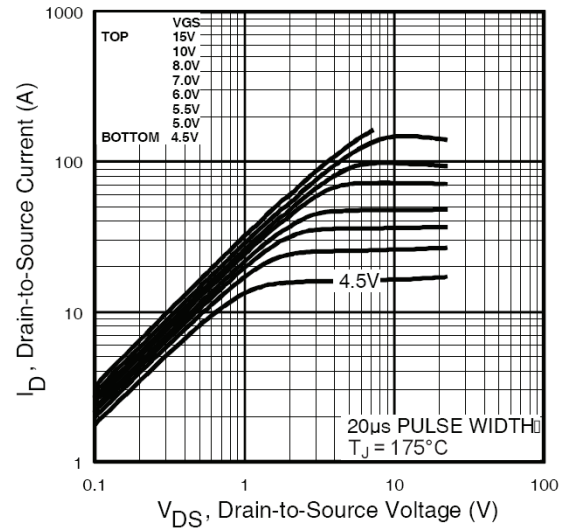
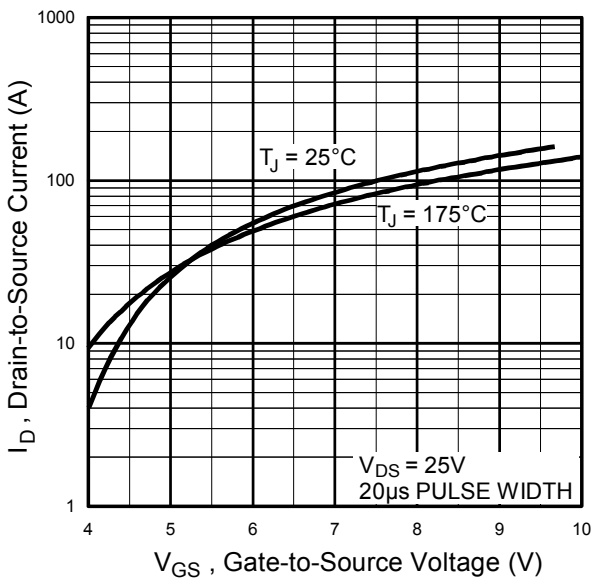
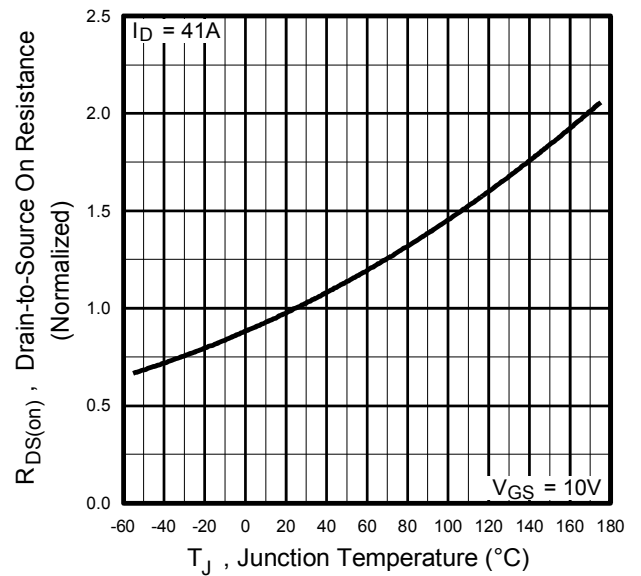
Q _g	Total Gate Charge	—	—	63	nC	I _D = 25A V _{DS} = 44V V _{GS} = 10V, See Fig. 6 and 13 ④
Q _{gs}	Gate-to-Source Charge	—	—	14		
Q _{gd}	Gate-to-Drain Charge	—	—	23		
t _{d(on)}	Turn-On Delay Time	—	12	—	ns	V _{DD} = 28V I _D = 25A R _G = 12Ω V _{GS} = 10V, See Fig. 10 ④
t _r	Rise Time	—	60	—		
t _{d(off)}	Turn-Off Delay Time	—	44	—		
t _f	Fall Time	—	45	—		
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	1470	—	pF	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz, See Fig. 5
C _{oss}	Output Capacitance	—	360	—		
C _{rss}	Reverse Transfer Capacitance	—	88	—		

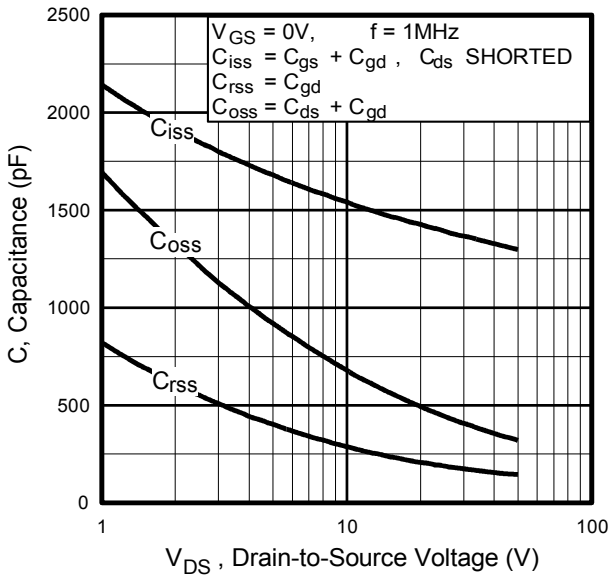
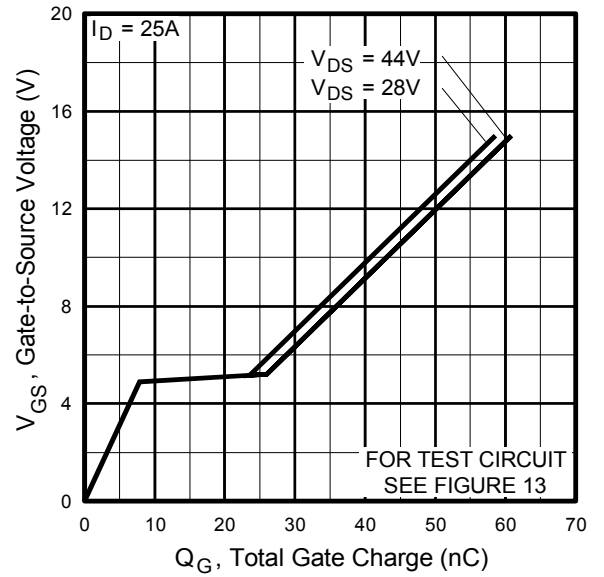
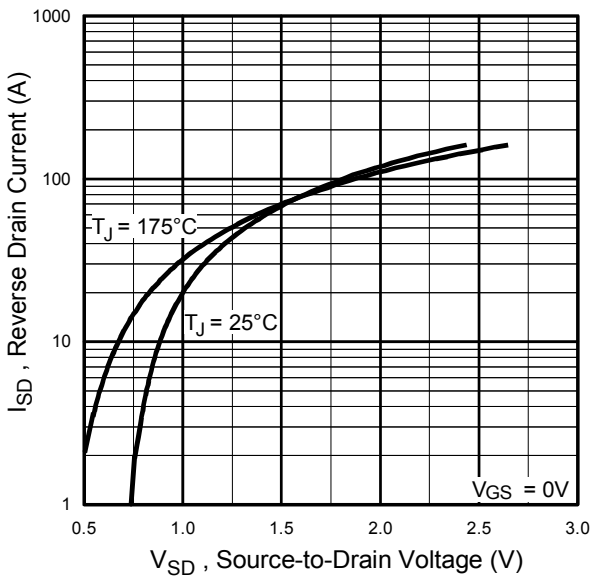
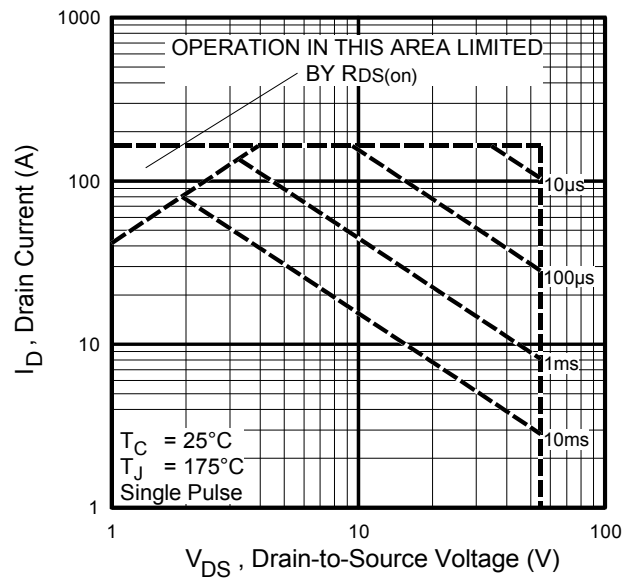
Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	49	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	160		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 25A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	63	95	ns	T _J = 25°C, I _F = 25A
Q _{rr}	Reverse Recovery Charge	—	170	260	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig.11)
- ② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.48mH, R_G = 25Ω, I_{AS} = 25A, V_{GS} = 10V. (See fig.12)
- ③ I_{SD} ≤ 25A, di/dt ≤ 230A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
- ④ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑤ This is a typical value at device destruction and represents operation outside rated limits.
- ⑥ This is a calculated value limited to T_J = 175°C.


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics

Fig. 3 Typical Transfer Characteristics

Fig. 4 Normalized On-Resistance vs. Temperature


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 7 Typical Source-to-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

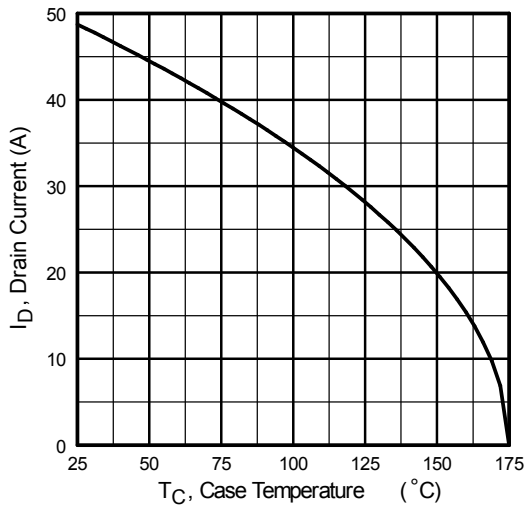


Fig 9. Maximum Drain Current vs. Case Temperature

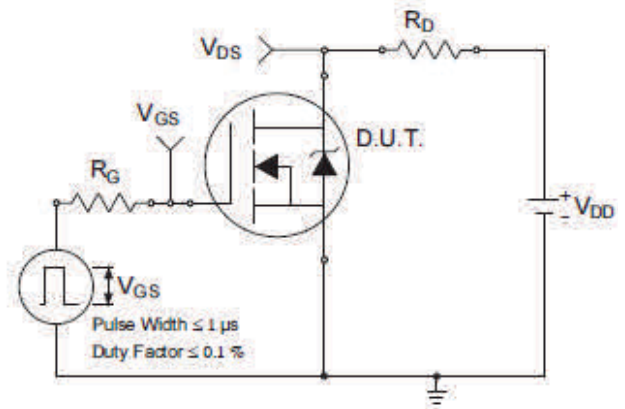


Fig 10a. Switching Time Test Circuit

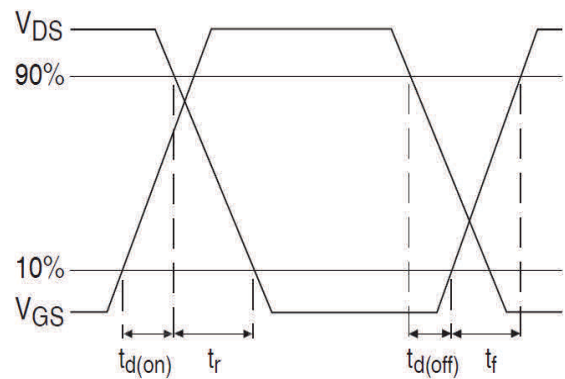


Fig 10b. Switching Time Waveforms

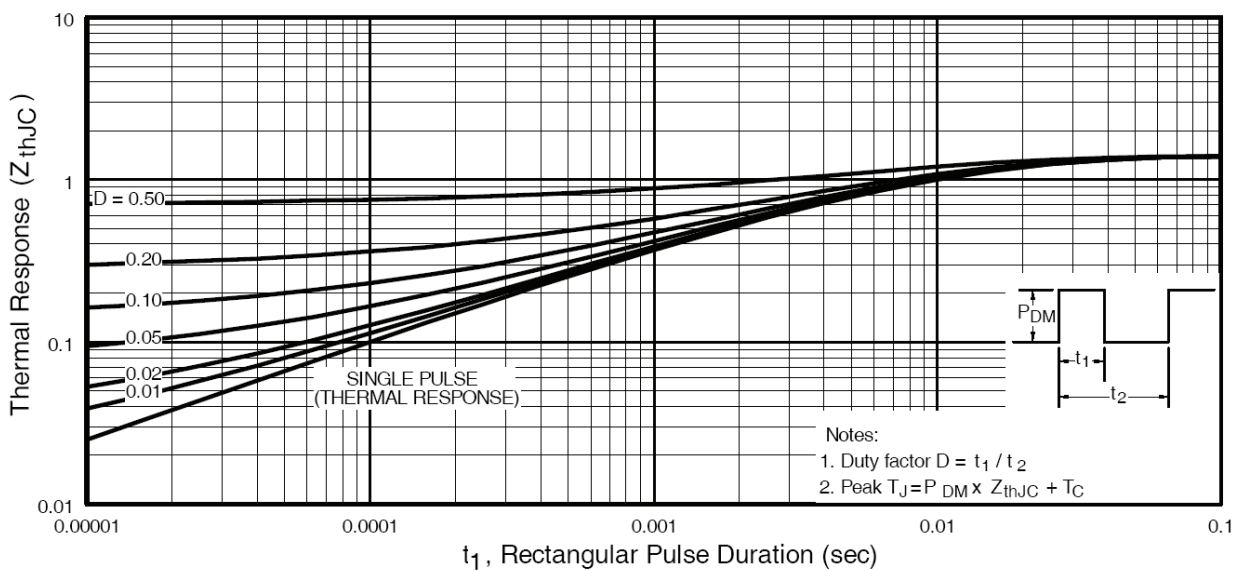


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

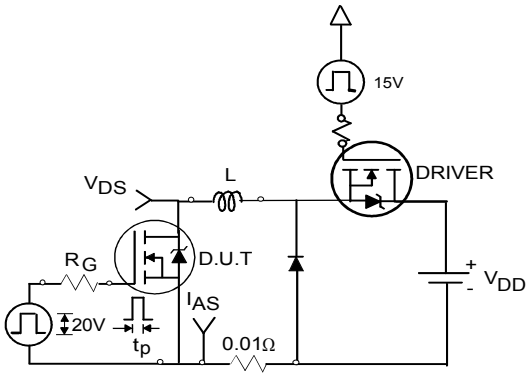


Fig 12a. Unclamped Inductive Test Circuit

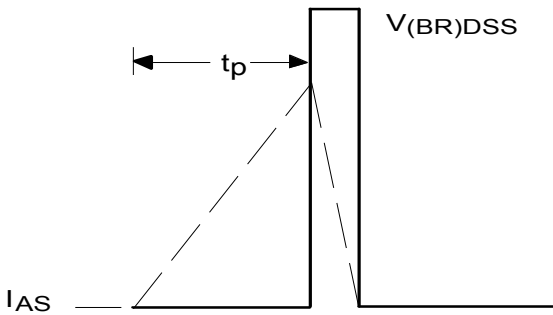


Fig 12b. Unclamped Inductive Waveforms

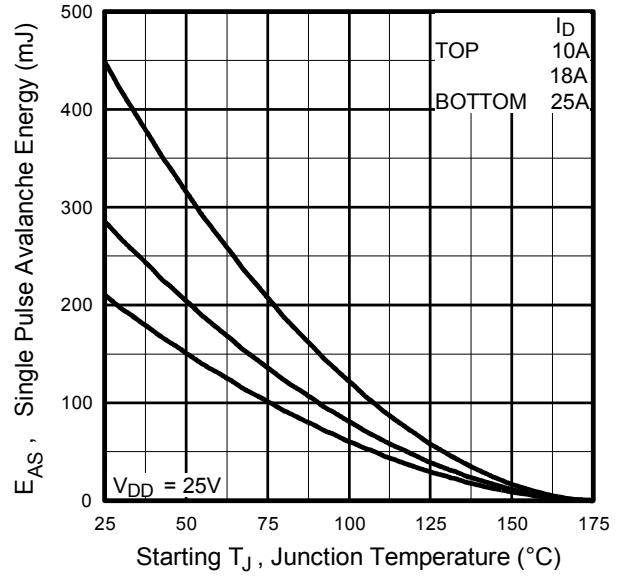


Fig 12c. Maximum Avalanche Energy vs. Drain Current

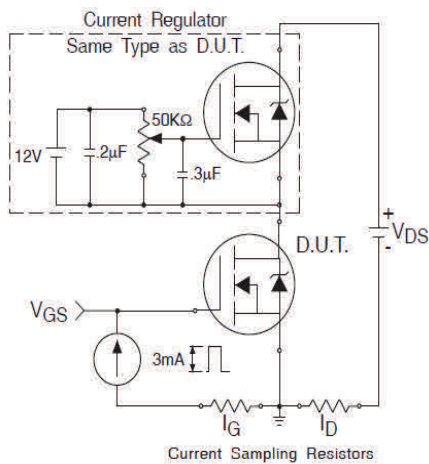


Fig 13a. Gate Charge Test Circuit

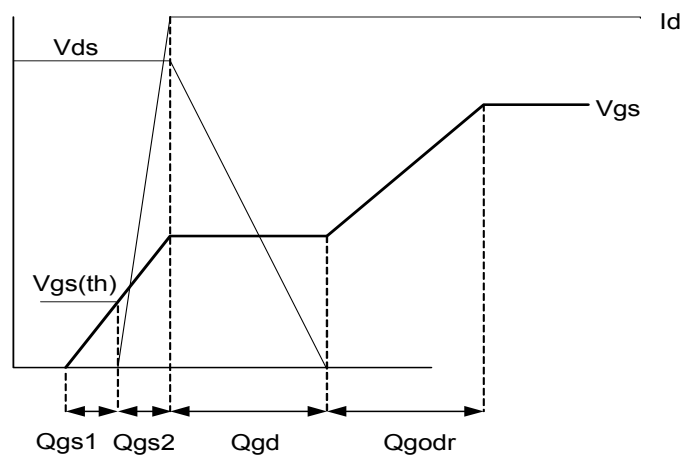
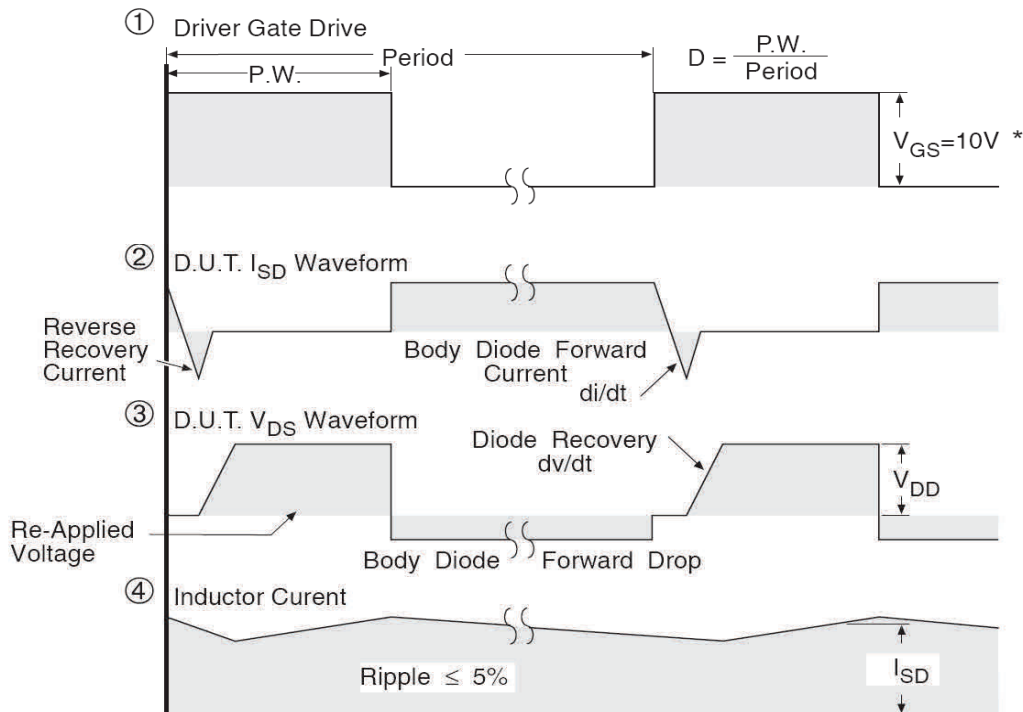
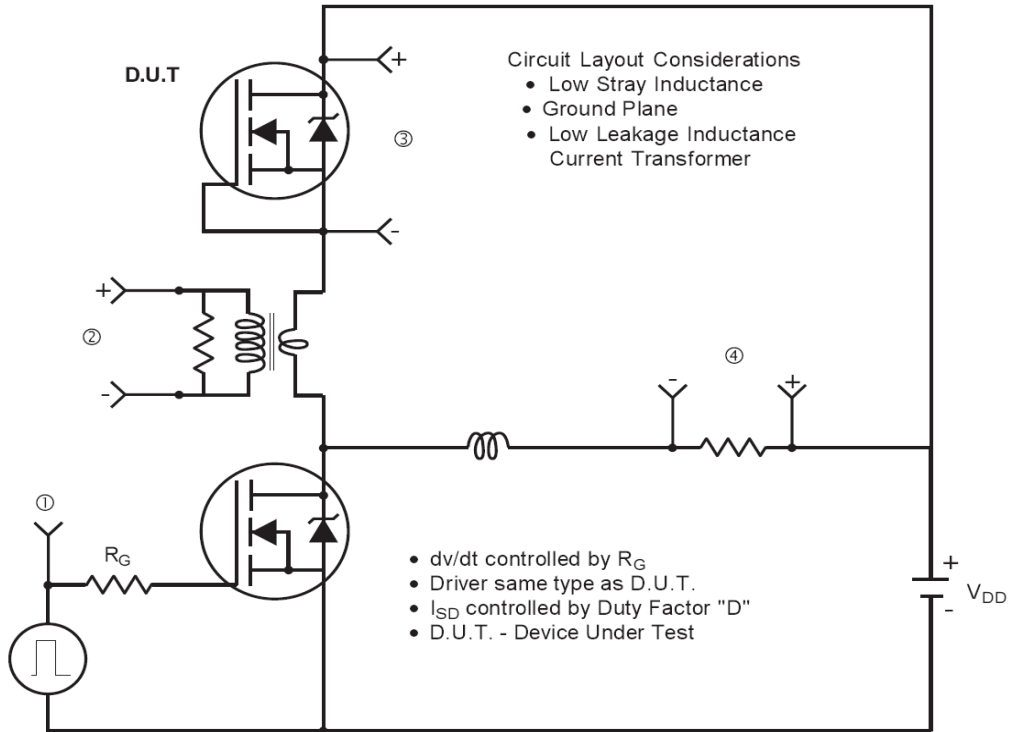


Fig 13b. Gate Charge Waveform

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

D²-Pak (TO-263AB) Package Outline (Dimensions are shown in millimeters (inches))


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
 4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
 5. DIMENSION b1, b3 AND c1 APPLY TO BASE METAL ONLY.
 6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 7. CONTROLLING DIMENSION: INCH.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	—	.245	—	4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	—	1.68	—	.066	4
L2	—	1.78	—	.070	
L3	0.25 BSC		.010 BSC		

LEAD ASSIGNMENTS
DIODES

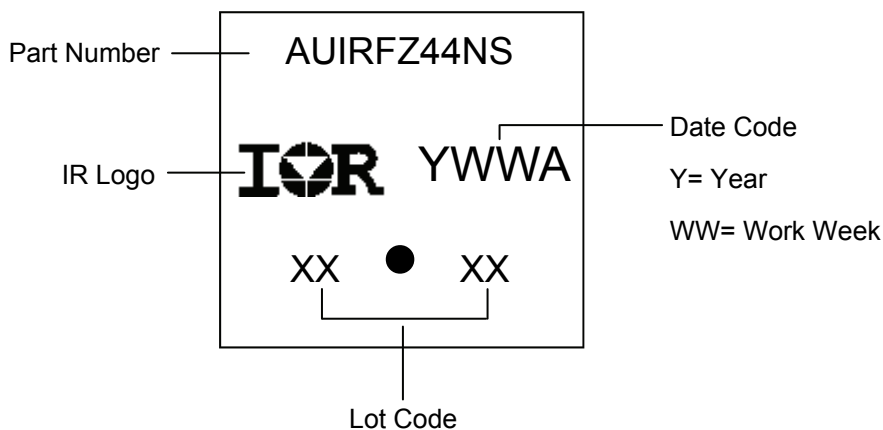
- 1.- ANODE (TWO DIE) / OPEN (ONE DIE)
- 2.- CATHODE
- 3.- ANODE

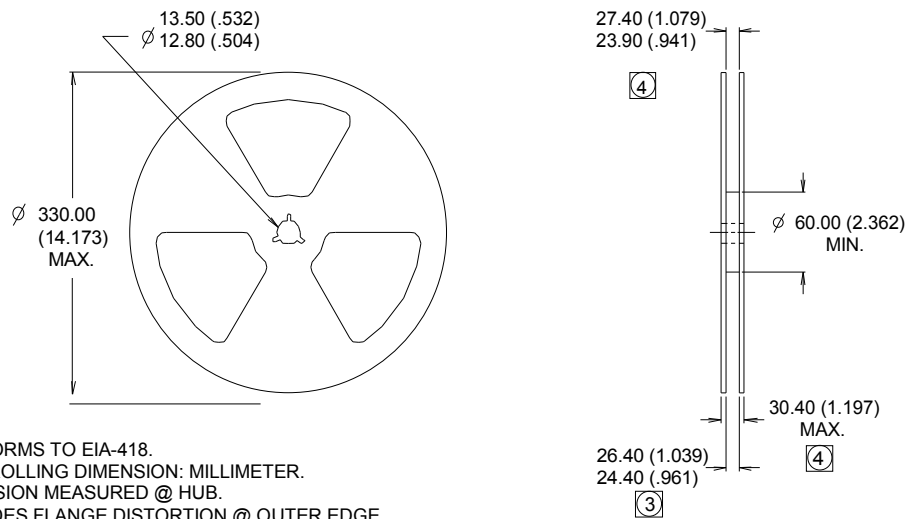
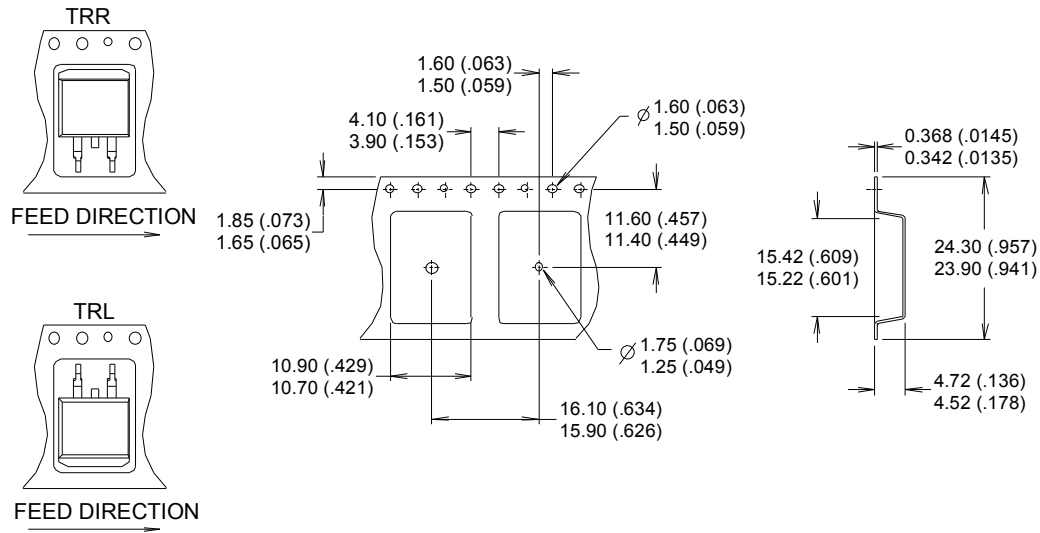
HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

D²-Pak (TO-263AB) Part Marking Information


D²Pak (TO-263AB) Tape & Reel Information (Dimensions are shown in millimeters (inches))


Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D ² -Pak	MSL1
ESD	Machine Model	Class M3 (+/- 400V) [†] AEC-Q101-002	
	Human Body Model	Class H1B (+/- 1000V) [†] AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) [†] AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Date	Comments
10/27/2015	<ul style="list-style-type: none"> Updated datasheet with corporate template Corrected ordering table on page 1.
10/25/2017	<ul style="list-style-type: none"> Removed TO-262 Pak "AUIRFL3207Z" this devices TO-262 Pak was never released and this part was erroneously added to the datasheet. –All pages Corrected typo error on part marking on page 8.

Published by

Infineon Technologies AG
81726 München, Germany

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